Rectifier diodes schottky barrier

PBYR4025WT series

GENERAL DESCRIPTION

Dual nickel silicide schottky barrier rectifier diodes in a plastic envelope featuring low forward voltage drop and absence of stored charge. These devices can withstand reverse voltage transients and have guaranteed reverse surge capability. The devices are intended for use in switched mode power supplies or as or-ing diodes in fault tolerant power supply systems.

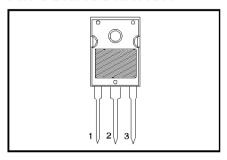
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	UNIT	
V _{RRM} V _F I _{O(AV)}	PBYR40- Repetitive peak reverse voltage Forward voltage Average output current (both diodes conducting)	20WT 20 0.46 40	25WT 25 0.46 40	V V A	

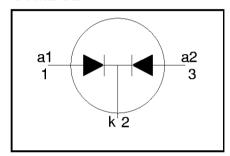
PINNING - SOT429 (TO247)

PIN	DESCRIPTION
1	Anode 1 (a)
2	Cathode (k)
3	Anode 2 (a)
mounting base	Cathode (k)

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT
V _{RRM} V _{RWM} V _R	Repetitive peak reverse voltage Crest working reverse voltage Continuous reverse voltage	T _{mb} ≤ 109 °C	1 1 1	-20 20 20 20	-25 25 25 25	V V
I _{O(AV)}	Average output current (both diodes conducting)	square wave; $\delta = 0.5$; $T_{mb} \le 128 ^{\circ}C$	-	4	0	A
I _{O(RMS)}	RMS output current (both diodes conducting)	1 mb = 120 0	-	5	7	Α
I _{FRM}		t = 25 μs; δ = 0.5; T _{mb} ≤ 128 °C	-	40		Α
I _{FSM}	Non-repetitive peak forward current, per diode	t = 10 ms t = 8.3 ms sinusoidal T _i = 125 °C prior to surge; with reapplied	-		30 00	A A
I ² t	I ² t for fusing	V _{RRM(max)} t = 10 ms	-	162		A ² s
I _{BBM}	Repetitive peak reverse current per diode	• ·	-		2	A
I _{RSM}	Non-repetitive peak reverse current per diode	$t_p = 100 \mu s$	-	2	2	Α
$\begin{matrix} T_{stg} \\ T_j \end{matrix}$	Storage temperature Operating junction temperature		-65 -		75 50	,C

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THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{ ext{th } j ext{-mb}}$	mounting base	per diode both diodes in free air	1 1 1	- - 45	1.5 1.0 -	K/W K/W K/W

STATIC CHARACTERISTICS

T_i = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{F}	Forward voltage (per diode)	I _F = 20 A; T _j = 125°C I _F = 40 A; T _j = 125°C	-	0.40	0.46	<<
		$I_F = 40 \text{ A}; I_j = 125 \text{ C}$ $I_F = 40 \text{ A}$	-	0.50 0.60	0.54 0.64	V
I _R	Reverse current (per diode)	$\dot{V}_{R} = V_{RRM}$	-	2.0	10	mA
C ^q	Junction capacitance (per diode)	$V_{R} = V_{RRM}^{\text{rinw}}; T_{j} = 100 ^{\circ}\text{C}$ $f = 1\text{MHz}; V_{R} = 5\text{V}; T_{j} = 25 ^{\circ}\text{C}$ to 125 $^{\circ}\text{C}$	-	30 900	80 -	mA pF

Philips Semiconductors Product specification

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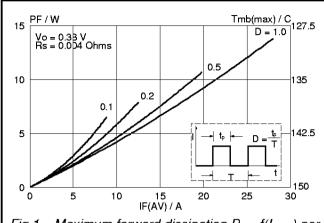
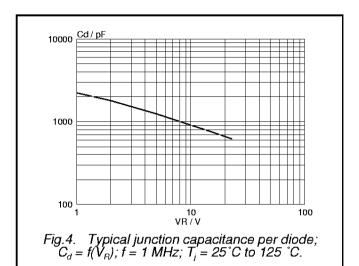


Fig.1. Maximum forward dissipation $P_F = f(I_{F(AV)})$ per diode; square current waveform where $I_{F(AV)} = I_{F(RMS)} \times \sqrt{D}$.



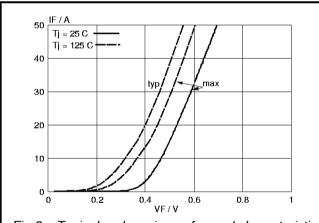


Fig.2. Typical and maximum forward characteristic $I_F = f(V_F)$; parameter T_i

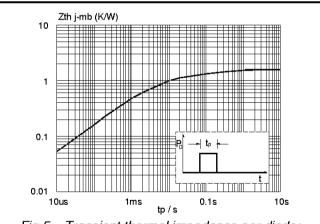


Fig.5. Transient thermal impedance per diode; $Z_{th,j,mb} = f(t_p)$.

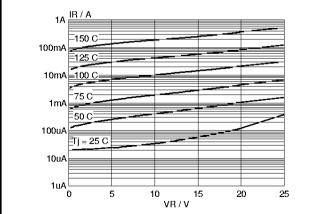
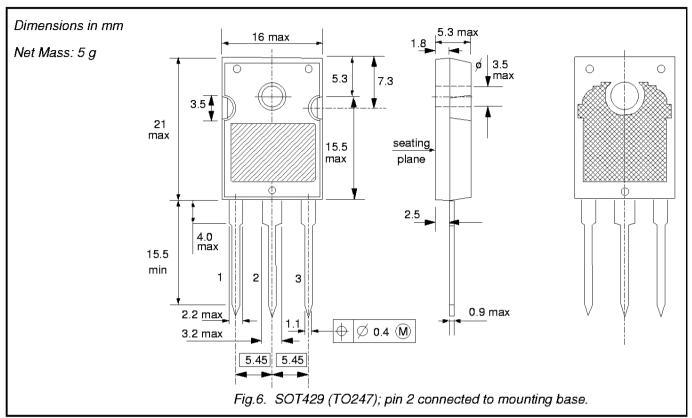


Fig.3. Typical reverse leakage current per diode; $I_R = f(V_R)$; parameter T_j

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MECHANICAL DATA



Notes

- Refer to mounting instructions for SOT429 envelope.
 Epoxy meets UL94 V0 at 1/8".

Philips Semiconductors Product specification

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DEFINITIONS

Data sheet status					
Objective specification This data sheet contains target or goal specifications for product development.					
Preliminary specification This data sheet contains preliminary data; supplementary data may be published la					
Product specification This data sheet contains final product specifications.					
Limiting values					

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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